

NCE N-Channel Super Trench Power MOSFET

Description

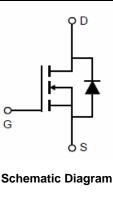
The NCEP30T12G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =30V, I_D =120A $R_{DS(ON)}$ =1.95m Ω (typical) @ V_{GS} =10V $R_{DS(ON)}$ =2.85m Ω (typical) @ V_{GS} =4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification







Top View

Bottom View

100% UIS TESTED!

100% AVds TESTED!

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| NCEP30T12G | NCEP30T12G | DFN5X6-8L | - | - | - |

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|------------|
| Drain-Source Voltage | V _{DS} | 30 | V |
| Gate-Source Voltage | V _{GS} | ±20 | V |
| Drain Current-Continuous (Silicon Limited) | I _D | 120 | Α |
| Drain Current-Continuous(T _C =100 °C) | I _D (100℃) | 84.8 | Α |
| Pulsed Drain Current (Package Limited) | I _{DM} | 340 | Α |
| Maximum Power Dissipation | P _D | 75 | W |
| Derating factor | | 0.6 | W/℃ |
| Single pulse avalanche energy (Note 5) | E _{AS} | 600 | mJ |
| Operating Junction and Storage Temperature Range | T_{J} , T_{STG} | -55 To 150 | $^{\circ}$ |



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NCEP30T12G

Thermal Characteristic

| Thermal Resistance, Junction-to-Case ^(Note 2) | R ₀ JC | 1.67 | °C/W | 1 |
|--|-------------------|------|------|---|
|--|-------------------|------|------|---|

Electrical Characteristics (T_C=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|---|---------------------|--|-----|------|----------|------|
| Off Characteristics | | | • | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 30 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V,V _{GS} =0V | - | - | 1 | μΑ |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 1.2 | 1.7 | 2.2 | V |
| Drain Course On State Begintanes | Б | V _{GS} =10V, I _D =60A | - | 1.95 | 2.35 | mΩ |
| Drain-Source On-State Resistance Forward Transconductance | R _{DS(ON)} | V _{GS} =4.5V, I _D =60A | - | 2.85 | 3.35 | mΩ |
| Forward Transconductance | g FS | V _{DS} =5V,I _D =60A | | 60 | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{lss} | V _{DS} =15V,V _{GS} =0V, | - | 3550 | 4200 | PF |
| Output Capacitance | Coss | | - | 950 | 1100 | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | - | 63 | 78 | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 9 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =15 V , I_D =60 A | - | 4 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10V, R_{G} =1.6 Ω | - | 44 | - | nS |
| Turn-Off Fall Time | t _f | | - | 7 | - | nS |
| Total Gate Charge | Qg | \/ -45\/ -00A | - | 63 | 72 | nC |
| Gate-Source Charge | Q_{gs} | $V_{DS}=15V,I_{D}=60A,$ | - | 10 | | nC |
| Gate-Drain Charge | Q_{gd} | V _{GS} =10V | - | 9.5 | | nC |
| Drain-Source Diode Characteristics | | | • | | <u>'</u> | |
| Diode Forward Voltage (Note 3) | V_{SD} | V _{GS} =0V,I _S =60A | - | | 1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 120 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = I _S | - | | 26 | nS |
| Reverse Recovery Charge | Qrr | $di/dt = 100A/\mu s^{(Note3)}$ | - | | 95 | nC |

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\mathrm{C}$,V_DD=15V,V_G=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics

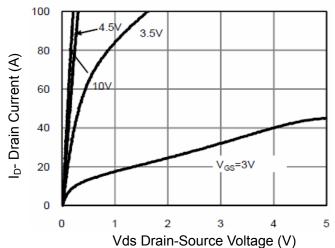


Figure 1 Output Characteristics

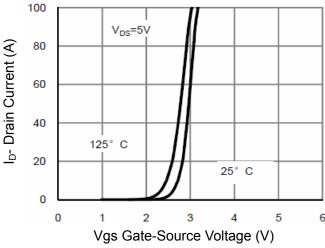


Figure 2 Transfer Characteristics

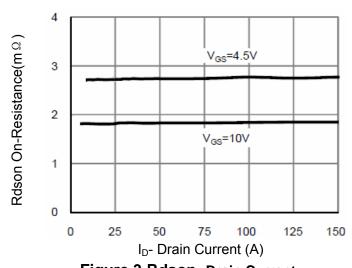


Figure 3 Rdson- Drain Current

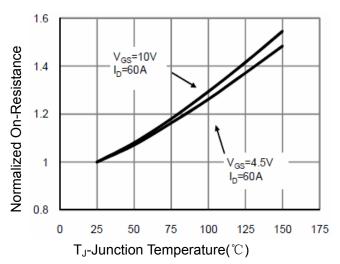


Figure 4 Rdson-Junction Temperature

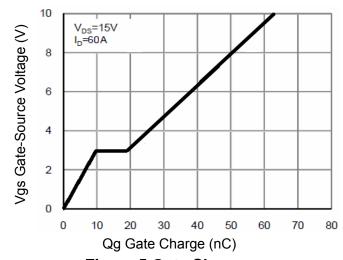


Figure 5 Gate Charge

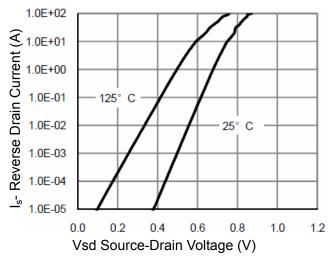


Figure 6 Source- Drain Diode Forward



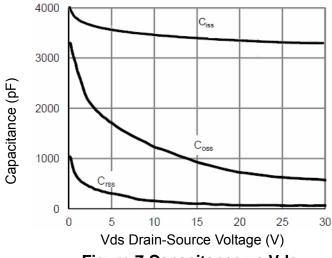


Figure 7 Capacitance vs Vds

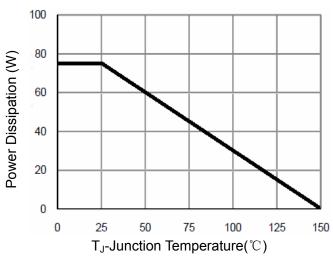


Figure 9 Power De-rating

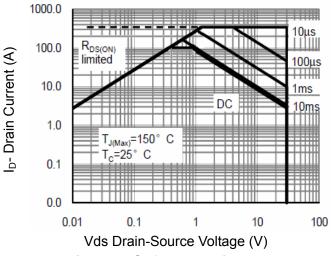


Figure 8 Safe Operation Area

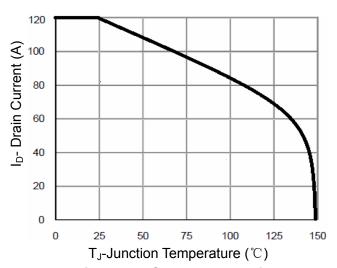


Figure 10 Current De-rating

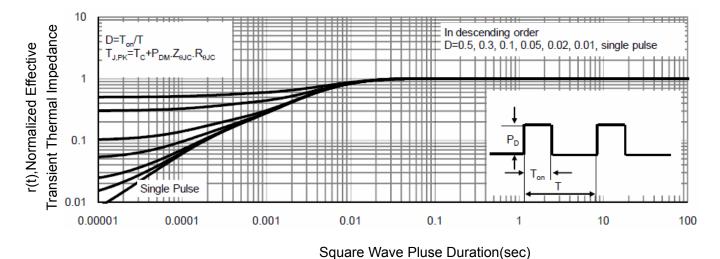


Figure 11 Normalized Maximum Transient Thermal Impedance



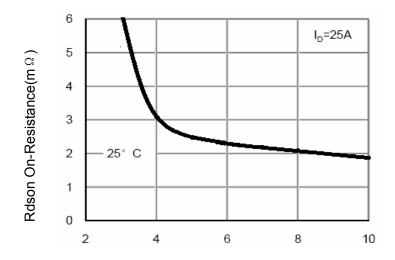
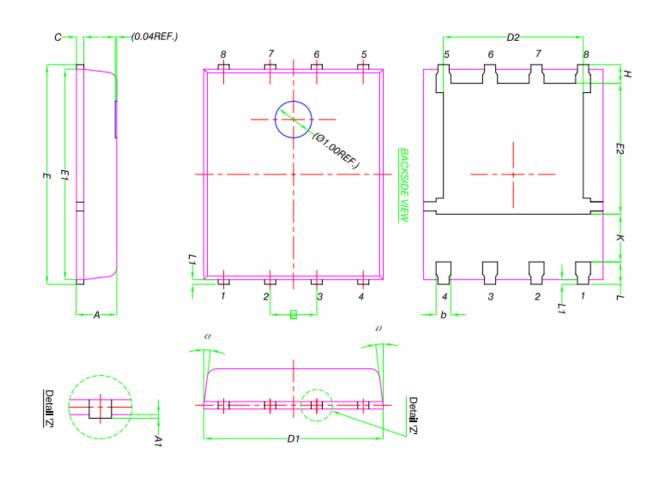


Figure 12 On-Resistance vs. Gate-Source Voltage

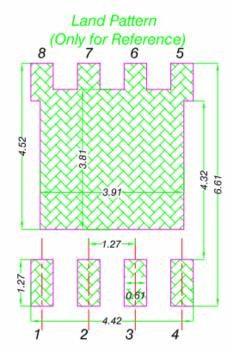
Vgs Gate-Source Voltage (V)



DFN5X6-8L Package Information



| | MILLIMETERS | | | |
|------|-------------|------|------|--|
| DIM. | MIN. | NOM. | MAX. | |
| Α | 0.90 | 1.00 | 1.10 | |
| A1 | 0 | - | 0.05 | |
| b | 0.33 | 0.41 | 0.51 | |
| С | 0.20 | 0.25 | 0.30 | |
| D1 | 4.80 | 4.90 | 5.00 | |
| D2 | 3.61 | 3.81 | 3.96 | |
| Ε | 5.90 | 6.00 | 6.10 | |
| E1 | 5.70 | 5.75 | 5.80 | |
| E2 | 3.38 | 3.58 | 3.78 | |
| е | 1.27 BSC | | | |
| Н | 0.41 0.51 | | 0.61 | |
| К | 1.10 | - | - | |
| L | 0.51 | 0.61 | 0.71 | |
| L1 | 0.06 | 0.13 | 0.20 | |
| α | 0° | - | 12° | |



Note:

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